

Applicant: Toshiki Makimoto, et al.  
 Serial No.: 10/516,380  
 Filing Date: November 30, 2004  
 For: P-TYPE NITRIDE SEMICONDUCTOR STRUCTURE AND BIPOLAR TRANSISTOR

Confirmation No.: 2860  
 Att'y Docket No.: 14321.63  
 Art Unit: 2818

### INFORMATION DISCLOSURE CITATIONS MADE BY APPLICANT

#### U.S. Patent Documents

<u>Examiner Initial*</u>	<u>Document Number</u>	<u>Issue Date</u>	<u>Name</u>
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#### Foreign Patent Documents

<u>Examiner Initial*</u>	<u>Document Number</u>	<u>Publication Date</u>	<u>Country or Patent Office</u>	<u>Translation</u>
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#### Other Documents

(including author, title, pertinent pages, etc.)

Examiner  
Initial\*

<u>/TN/</u> 1	T. Makimoto, et al., <i>High Current Gains Obtained by InGaN/GaN Double Heterojunction Bipolar Transistors with P-InGaN Base</i> , Applied Physics Letters, 79, No. 3, pp. 380-381, July 16, 2001.
<u>/TN/</u> 2	Supplementary European Search Report of related European Application No. 04700296.9, dated April 6, 2009 (2 pages).

### **References Cited by Applicants**

While the filing of Information Disclosure Statements is voluntary, the procedure is governed by the guidelines of Section 609 of the Manual of Patent Examining Procedure and 37 C.F.R. §§ 1.97 and 1.98. To be considered a proper Information Disclosure Statement, Form PTO-1449 shall be accompanied by a copy of each listed patent or publication or other item of information and a translation of the pertinent portions of foreign documents (if an existing translation is readily available to the applicant), an explanation of relevance of each reference not in the English language, and should be submitted in a timely manner as set out in MPEP Sec. 609.

Examiner:	<u>/Tram Nguyen/</u>	Date Considered:	<u>05/26/2009</u>
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609, draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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Examiners will consider all citations submitted in conformance with 37 C.F.R. § 1.98 and MPEP Sec. 609 and place their initials adjacent the citations in the spaces provided on this form. Examiners will also initial citations not in conformance with the guidelines which may have been considered. A reference may be considered by the Examiner for any reason whether or not the citation is in full conformance with the guidelines. A line will be drawn through a citation if it is not in conformance with the guidelines AND has not been considered. A copy of the submitted form, as reviewed by the Examiner, will be returned to the applicant with the next communication. The original of the form will be entered into the application file.

Each citation initialed by the Examiner will be printed on the issued patent in the same manner as references cited by the Examiner on Form PTO-892.

The reference designations "A1," "A2," etc. (referring to Applicant's reference 1, Applicant's reference 2, etc.) will be used by the Examiner in the same manner as Examiner's reference designations "A," "B," "C," etc. on Office Action Form PTO-1142.

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Examiner: /Tram Nguyen/

Date Considered:

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